Dan Fleetwood

List of Publications by Year
in descending order

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312	10,124	53	86
papers	citations	h-index	g-index

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51492

312	312	312	4713
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Radiation Effects in MOS Oxides. IEEE Transactions on Nuclear Science, 2008, 55, 1833-1853.	1.2	676
2	Effects of oxide traps, interface traps, and â€˜â€˜border trapsâ€™â€™ on metalâ€oxideâ€semiconductor devices. Journal of Applied Physics, 1993, 73, 5058-5074.	1.1	526
3	Total Ionizing Dose Effects in MOS and Low-Dose-Rate-Sensitive Linear-Bipolar Devices. IEEE Transactions on Nuclear Science, 2013, 60, 1706-1730.	1.2	276
4	Non-volatile memory device based on mobile protons in SiO2 thin films. Nature, 1997, 386, 587-589.	13.7	216
5	Structure, Properties, and Dynamics of Oxygen Vacancies in AmorphousSiO2. Physical Review Letters, 2002, 89, 285505.	2.9	167
6	Defect Generation by Hydrogen at the Si-SiO2Interface. Physical Review Letters, 2001, 87, 165506.	2.9	159
7	Estimating oxideâ€trap, interfaceâ€trap, and borderâ€trap charge densities in metalâ€oxideâ€semiconductor transistors. Applied Physics Letters, 1994, 64, 1965-1967.	1.5	145
8	<formula formulatype="inline"><tex Notation="TeX">$1/f$</tex></formula> Noise and Defects in Microelectronic Materials and Devices. IEEE Transactions on Nuclear Science, 2015, 62, 1462-1486.	1.2	143
9	Evidence that similar point defects cause 1/fnoise and radiation-induced-hole trapping in metal-oxide-semiconductor transistors. Physical Review Letters, 1990, 64, 579-582.	2.9	138
10	Oxide, interface, and border traps in thermal, N2O, and N2Oâ€nitrided oxides. Journal of Applied Physics, 1996, 79, 1583-1594.	1.1	136
11	Proton-Induced Dehydrogenation of Defects in AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2013, 60, 4080-4086.	1.2	136
12	ELDRS in Bipolar Linear Circuits: A Review. IEEE Transactions on Nuclear Science, 2009, 56, 1894-1908.	1.2	128
13	Evolution of Total Ionizing Dose Effects in MOS Devices With Mooreâ€™s Law Scaling. IEEE Transactions on Nuclear Science, 2018, 65, 1465-1481.	1.2	128
14	Electron-Induced Single-Event Upsets in Static Random Access Memory. IEEE Transactions on Nuclear Science, 2013, 60, 4122-4129.	1.2	121
15	Effect of postâ€oxidation anneal temperature on radiationâ€induced charge trapping in metalâ€oxideâ€semiconductor devices. Applied Physics Letters, 1988, 53, 770-772.	1.5	115
16	Dehydrogenation of defects and hot-electron degradation in GaN high-electron-mobility transistors. Journal of Applied Physics, 2011, 109, .	1.1	114
17	Radiation Effects in Advanced Multiple Gate and Silicon-on-Insulator Transistors. IEEE Transactions on Nuclear Science, 2013, 60, 1970-1991.	1.2	114
18	Physical mechanisms of negative-bias temperature instability. Applied Physics Letters, 2005, 86, 142103.	1.5	113

#	Article	IF	Citations
19	Total ionizing dose effects in shallow trench isolation oxides. Microelectronics Reliability, 2008, 48, 1000-1007.	0.9	110
20	Radiationâ€induced charge neutralization and interfaceâ€trap buildup in metalâ€oxideâ€semiconductor devices. Journal of Applied Physics, 1990, 67, 580-583.	1.1	105
21	The Role of Hydrogen in Radiation-Induced Defect Formation in Polysilicon Gate MOS Devices. IEEE Transactions on Nuclear Science, 1987, 34, 1152-1158.	1.2	104
22	Point defect generation during high temperature annealing of the Siâ€SiO2interface. Applied Physics Letters, 1993, 63, 2926-2928.	1.5	98
23	A Reevaluation of Worst-Case Postirradiation Response for Hardened MOS Transistors. IEEE Transactions on Nuclear Science, 1987, 34, 1178-1183.	1.2	91
24	Total-Dose Radiation and Annealing Studies: Implications for Hardness Assurance Testing. IEEE Transactions on Nuclear Science, 1986, 33, 1343-1351.	1.2	90
25	Direct link between1/fnoise and defects in metal films. Physical Review B, 1985, 31, 1157-1160.	1.1	88
26	Effects of Total Dose Irradiation on the Gate-Voltage Dependence of the $hbox{1}/f$ Noise of nMOS and pMOS Transistors. IEEE Transactions on Electron Devices, 2010, 57, 503-510.	1.6	84
27	Effects of Applied Bias and High Field Stress on the Radiation Response of GaN/AlGaN HEMTs. IEEE Transactions on Nuclear Science, 2015, 62, 2423-2430.	1.2	84
28	Temperature-independent switching rates for a random telegraph signal in a silicon metalâ€“oxideâ€“semiconductor field-effect transistor at low temperatures. Applied Physics Letters, 2000, 76, 3248-3250.	1.5	83
29	Optimizing and Controlling the Radiation Hardness of a Si-Gate CMOS Process. IEEE Transactions on Nuclear Science, 1985, 32, 3953-3960.	1.2	77
30	Fin-Width Dependence of Ionizing Radiation-Induced Subthreshold-Swing Degradation in 100-nm-Gate-Length FinFETs. IEEE Transactions on Nuclear Science, 2009, 56, 3250-3255.	1.2	76
31	An overview of radiation effects on electronics in the space telecommunications environment. Microelectronics Reliability, 2000, 40, 17-26.	0.9	75
32	Radiation Induced Charge Trapping in Ultrathin ${m HfO}_{2}$-Based MOSFETs. IEEE Transactions on Nuclear Science, 2007, 54, 1883-1890.	1.2	74
33	Influence of LDD Spacers and H⁺Transport on the Total-Ionizing-Dose Response of 65-nm MOSFETs Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2018, 65, 164-174.	1.2	73
34	Accounting for Dose-Enhancement Effects with CMOS Transistors. IEEE Transactions on Nuclear Science, 1985, 32, 4369-4375.	1.2	70
35	Radiation-Induced Defect Evolution and Electrical Degradation of AlGaN/GaN High-Electron-Mobility Transistors. IEEE Transactions on Nuclear Science, 2011, 58, 2918-2924.	1.2	69
36	Temperature Dependence and Postirradiation Annealing Response of the $1/f$ Noise of 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2013, 60, 2361-2367.	1.6	69

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37	Total-Ionizing-Dose Effects, Border Traps, and 1/<i>f</i> Noise in Emerging MOS Technologies. IEEE Transactions on Nuclear Science, 2020, 67, 1216-1240.	1.2	68
38	Characterizing SRAM Single Event Upset in Terms of Single and Multiple Node Charge Collection. IEEE Transactions on Nuclear Science, 2008, 55, 2943-2947.	1.2	67
39	Links between oxide, interface, and border traps in highâ€temperature annealed Si/SiO2systems. Applied Physics Letters, 1994, 64, 3452-3454.	1.5	62
40	Correlation between latent interface trap buildup and 1/fnoise in metalâ€"oxideâ€"semiconductor transistors. Applied Physics Letters, 1997, 70, 1158-1160.	1.5	60
41	Electron Capture, Hydrogen Release, and Enhanced Gain Degradation in Linear Bipolar Devices. IEEE Transactions on Nuclear Science, 2008, 55, 2986-2991.	1.2	59
42	Impact of proton irradiation on deep level states in n-GaN. Applied Physics Letters, 2013, 103, .	1.5	59
43	A Quantitative Model for ELDRS and ${m H}_{2}$ Degradation Effects in Irradiated Oxides Based on First Principles Calculations. IEEE Transactions on Nuclear Science, 2011, 58, 2937-2944.	1.2	58
44	1/f Noise in GaN HEMTs grown under Ga-rich, N-rich, and NH3-rich conditions. Microelectronics Reliability, 2011, 51, 212-216.	0.9	58
45	The Impact of X-Ray and Proton Irradiation on ${m HfO}_2/{m Hf}$-Based Bipolar Resistive Memories. IEEE Transactions on Nuclear Science, 2013, 60, 4540-4546.	1.2	58
46	Electrostatic Mechanisms Responsible for Device Degradation in Proton Irradiated AlGaN/AlN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2008, 55, 2106-2112.	1.2	57
47	Bias Dependence of Total Ionizing Dose Effects in SiGe-MOS FinFETs<formula formulatype="inline"> <tex Notation="TeX"/> </formula>. IEEE Transactions on Nuclear Science, 2014, 61, 2834-2838.	1.2	57
48	Radiation-Induced Interface-State Generation in MOS Devices. IEEE Transactions on Nuclear Science, 1986, 33, 1177-1184.	1.2	56
49	Low-Energy X-ray and Ozone-Exposure Induced Defect Formation in Graphene Materials and Devices. IEEE Transactions on Nuclear Science, 2011, 58, 2961-2967.	1.2	56
50	The role of temperature in sampleâ€toâ€sample comparisons of the 1/fnoise of metal films. Journal of Applied Physics, 1987, 61, 5308-5313.	1.1	55
51	Total-Ionizing-Dose Radiation Effects in AlGaN/GaN HEMTs and MOS-HEMTs. IEEE Transactions on Nuclear Science, 2013, 60, 4074-4079.	1.2	55
52	Geometry Dependence of Total-Dose Effects in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2951-2958.	1.2	54
53	Effects of Proton-Induced Displacement Damage on Gallium Nitride HEMTs in RF Power Amplifier Applications. IEEE Transactions on Nuclear Science, 2015, 62, 2417-2422.	1.2	53
54	Electrical-stress-induced degradation in AlGaN/GaN high electron mobility transistors grown under gallium-rich, nitrogen-rich, and ammonia-rich conditions. Applied Physics Letters, 2010, 96, .	1.5	50

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55	Physical Processes and Applications of the Monte Carlo Radiative Energy Deposition (MRED) Code. IEEE Transactions on Nuclear Science, 2015, 62, 1441-1461.	1.2	50
56	Charge Trapping in Al₂O₃/eta -Ga₂O₃-Based MOS Capacitors. IEEE Electron Device Letters, 2018, 39, 1022-1025.	2.2	50
57	Radiation Effects in a Post-Moore World. IEEE Transactions on Nuclear Science, 2021, 68, 509-545.	1.2	50
58	Longâ€term annealing study of midgap interfaceâ€trap charge neutrality. Applied Physics Letters, 1992, 60, 2883-2885.	1.5	49
59	Process Dependence of Proton-Induced Degradation in GaN HEMTs. IEEE Transactions on Nuclear Science, 2010, , .	1.2	49
60	Multiple Defects Cause Degradation After High Field Stress in AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2018, 18, 364-376.	1.5	49
61	Comparison of Charge Pumping and <formula formulatype="inline"> <tex Notation="TeX">$1/f$</tex> </formula> Noise in Irradiated Ge pMOSFETs. IEEE Transactions on Nuclear Science, 2012, 59, 735-741.	1.2	47
62	An Investigation of Dose Rate and Source Dependent Effects in 200 GHz SiGe HBTs. IEEE Transactions on Nuclear Science, 2006, 53, 3166-3174.	1.2	46
63	Worst-Case Bias for Proton and 10-keV X-Ray Irradiation of AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2017, 64, 218-225.	1.2	46
64	Determining the energy distribution of traps in insulating thin films using the thermally stimulated current technique. Physical Review Letters, 1992, 69, 820-823.	2.9	45
65	Theory of hot-carrier-induced phenomena in GaN high-electron-mobility transistors. Applied Physics Letters, 2010, 96, .	1.5	45
66	Role of Fe impurity complexes in the degradation of GaN/AlGaN high-electron-mobility transistors. Applied Physics Letters, 2015, 106, .	1.5	45
67	Temperature-dependence and microscopic origin of low frequency 1/<i>f</i> noise in GaN/AlGaN high electron mobility transistors. Applied Physics Letters, 2011, 99, .	1.5	44
68	1fNoise in Platinum Films and Ultrathin Platinum Wires: Evidence for a Common, Bulk Origin. Physical Review Letters, 1983, 50, 450-453.	2.9	43
69	Effect of strain on the1fnoise of metal films. Physical Review B, 1983, 28, 3625-3627.	1.1	43
70	Thermally stimulated current measurements of SiO2 defect density and energy in irradiated metalâ€oxideâ€semiconductor capacitors. Review of Scientific Instruments, 1992, 63, 5714-5725.	0.6	43
71	Heavy-Ion-Induced Current Transients in Bulk and SOI FinFETs. IEEE Transactions on Nuclear Science, 2012, 59, 2674-2681.	1.2	43
72	Bulk oxide traps and border traps in metalâ€“oxideâ€“semiconductor capacitors. Journal of Applied Physics, 1998, 84, 6141-6148.	1.1	41

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73	Hydrogen-Related Instabilities in MOS Devices Under Bias Temperature Stress. IEEE Transactions on Device and Materials Reliability, 2007, 7, 502-508.	1.5	40
74	Gate Bias Dependence of Defect-Mediated Hot-Carrier Degradation in GaN HEMTs. IEEE Transactions on Electron Devices, 2014, 61, 1316-1320.	1.6	40
75	Effects of Switched-bias Annealing on Charge Trapping in HfO$_{2}$ Gate Dielectrics. IEEE Transactions on Nuclear Science, 2006, 53, 3636-3643.	1.2	39
76	Total-Ionizing-Dose Effects on Threshold Switching in $1{T}$ -TaS2 Charge Density Wave Devices. IEEE Electron Device Letters, 2017, 38, 1724-1727.	2.2	39
77	Defects and Low-Frequency Noise in Irradiated Black Phosphorus MOSFETs With HfO₂ Gate Dielectrics. IEEE Transactions on Nuclear Science, 2018, 65, 1227-1238.	1.2	39
78	Ozone-exposure and annealing effects on graphene-on-SiO2 transistors. Applied Physics Letters, 2012, 101, .	1.5	38
79	Effects of Bias on the Irradiation and Annealing Responses of 4H-SiC MOS Devices. IEEE Transactions on Nuclear Science, 2011, 58, 2925-2929.	1.2	37
80	The Effects of Proton-Defect Interactions on Radiation-Induced Interface-Trap Formation and Annealing. IEEE Transactions on Nuclear Science, 2012, 59, 3087-3092.	1.2	37
81	Origins of Low-Frequency Noise and Interface Traps in 4H-SiC MOSFETs. IEEE Electron Device Letters, 2013, 34, 117-119.	2.2	37
82	Total Dose Radiation Response of Nitrided and Non-nitrided SiO$_{2}$/4H-SiC MOS Capacitors. IEEE Transactions on Nuclear Science, 2006, 53, 3687-3692.	1.2	36
83	Dual behavior of H+ at Siâ€“SiO2 interfaces: Mobility versus trapping. Applied Physics Letters, 2002, 81, 1839-1841.	1.5	35
84	Bias Dependence of Total-Dose Effects in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2013, 60, 4476-4482.	1.2	35
85	Correlation of proton irradiation induced threshold voltage shifts to deep level traps in AlGaN/GaN heterostructures. Journal of Applied Physics, 2016, 119, .	1.1	35
86	Ionizing-Radiation Response and Low-Frequency Noise of 28-nm MOSFETs at Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2020, 67, 1302-1311.	1.2	35
87	Resistivity dependence of1fnoise in metal films. Physical Review B, 1983, 27, 667-671.	1.1	34
88	Fin Width and Bias Dependence of the Response of Triple-Gate MOSFETs to Total Dose Irradiation. IEEE Transactions on Nuclear Science, 2011, 58, 2871-2875.	1.2	34
89	Room-temperature diffusive phenomena in semiconductors: The case of AlGaN. Physical Review B, 2011, 84, .	1.1	32
90	Radiation Effects in AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2022, 69, 1105-1119.	1.2	32

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91	Atomic-scale origins of bias-temperature instabilities in SiCâ€"SiO2 structures. Applied Physics Letters, 2011, 98, .	1.5	31
92	1/ f Noise in As-Processed and Proton-Irradiated AlGaN/GaN HEMTs Due to Carrier Number Fluctuations. IEEE Transactions on Nuclear Science, 2017, 64, 181-189.	1.2	31
93	Random telegraph signals in n-type ZnO nanowire field effect transistors at low temperature. Applied Physics Letters, 2007, 91, .	1.5	30
94	Hydrogen shuttling near Hf-defect complexes in Siâˆ•SiO2âˆ•HfO2 structures. Applied Physics Letters, 2007, 91, .	1.5	30
95	Accounting for time-dependent effects on CMOS total-dose response in space environments. Radiation Physics and Chemistry, 1994, 43, 129-138.	1.4	29
96	Characterization of multiple Siâˆ•SiO2 interfaces in silicon-on-insulator materials via second-harmonic generation. Applied Physics Letters, 2004, 85, 3095-3097.	1.5	29
97	Proton-irradiation-immune electronics implemented with two-dimensional charge-density-wave devices. Nanoscale, 2019, 11, 8380-8386.	2.8	29
98	Total-Ionizing-Dose Effects and Low-Frequency Noise in 30-nm Gate-Length Bulk and SOI FinFETs With SiO₂/HfO₂Gate Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 245-252.	1.2	29
99	Temperature dependence of the 1/fnoise of carbon resistors. Journal of Applied Physics, 1984, 56, 3256-3260.	1.1	28
100	Impact of Proton Irradiation-Induced Bulk Defects on Gate-Lag in GaN HEMTs. IEEE Transactions on Nuclear Science, 2009, 56, 3192-3195.	1.2	28
101	Total Ionizing Dose (TID) Effects in Extremely Scaled Ultra-Thin Channel Nanowire (NW) Gate-All-Around (GAA) InGaAs MOSFETs. IEEE Transactions on Nuclear Science, 2015, 62, 2888-2893.	1.2	28
102	Total Ionizing Dose Effects on Strained Ge pMOS FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2017, 64, 226-232.	1.2	28
103	Dose-Rate Sensitivity of 65-nm MOSFETs Exposed to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2018, 65, 1482-1487.	1.2	28
104	TID and Displacement Damage Resilience of 1T1R <formula formulatype="inline"><tex Notation="TeX">${m HfO}_2/{m Hf}$</tex></formula> Resistive Memories. IEEE Transactions on Nuclear Science, 2014, 61, 2972-2978.	1.2	27
105	Total Ionizing Dose Effects on hBN Encapsulated Graphene Devices. IEEE Transactions on Nuclear Science, 2014, 61, 2868-2873.	1.2	27
106	Hot-Carrier Degradation in GaN HEMTs Due to Substitutional Iron and Its Complexes. IEEE Transactions on Electron Devices, 2016, 63, 1486-1494.	1.6	27
107	Differences Between Charge Trapping States in Irradiated Nano-Crystalline HfO$_{2}$ and Non-Crystalline Hf Silicates. IEEE Transactions on Nuclear Science, 2006, 53, 3644-3648.	1.2	26
108	Total Ionizing Dose Effects on<newline/> Silicon Ring Resonators. IEEE Transactions on Nuclear Science, 2015, 62, 323-328.	1.2	26

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109	Charge Buildup and Spatial Distribution of Interface Traps in 65-nm pMOSFETs Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2019, 66, 1574-1583.	1.2	26
110	Total-Ionizing-Dose Effects and Low-Frequency Noise in 16-nm InGaAs FinFETs With HfO₂/Al₂O₃ Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 210-220.	1.2	26
111	Effects of Water on the Aging and Radiation Response of MOS Devices. IEEE Transactions on Nuclear Science, 2006, 53, 3629-3635.	1.2	25
112	Mechanisms Separating Time-Dependent and True Dose-Rate Effects in Irradiated Bipolar Oxides. IEEE Transactions on Nuclear Science, 2012, 59, 3069-3076.	1.2	25
113	Time-Domain Reflectometry Measurements of Total-Ionizing-Dose Degradation of nMOSFETs. IEEE Transactions on Nuclear Science, 2013, 60, 4470-4475.	1.2	25
114	Charge Collection Mechanisms in AlGaN/GaN MOS High Electron Mobility Transistors. IEEE Transactions on Nuclear Science, 2013, 60, 4439-4445.	1.2	25
115	High-Field Stress, Low-Frequency Noise, and Long-Term Reliability of AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 282-289.	1.5	25
116	Charge Trapping Properties of 3C- and 4H-SiC MOS Capacitors With Nitrided Gate Oxides. IEEE Transactions on Nuclear Science, 2009, 56, 3185-3191.	1.2	24
117	SEB Hardened Power MOSFETs With High-K Dielectrics. IEEE Transactions on Nuclear Science, 2015, 62, 2830-2836.	1.2	24
118	Dose-Rate Dependence of the Total-Ionizing-Dose Response of GaN-Based HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 170-176.	1.2	24
119	Atomic Displacement Effects in Single-Event Gate Rupture. IEEE Transactions on Nuclear Science, 2008, 55, 3025-3031.	1.2	23
120	Thermal stability of deep level defects induced by high energy proton irradiation in n-type GaN. Journal of Applied Physics, 2015, 118, .	1.1	23
121	Temperature-Dependent Efficiency Droop in GaN-Based Blue LEDs. IEEE Electron Device Letters, 2018, 39, 528-531.	2.2	23
122	Stability of trapped electrons in SiO2. Applied Physics Letters, 1999, 74, 2969-2971.	1.5	22
123	Dual role of fluorine at the Siâ€"SiO2 interface. Applied Physics Letters, 2004, 85, 4950-4952.	1.5	22
124	Total Dose Response of Ge MOS Capacitors With HfO$_{2}$/Dy$_{2}$O$_{3}$ Gate Stacks. IEEE Transactions on Nuclear Science, 2007, 54, 971-974.	1.2	22
125	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2014, 61, 3210-3217.	1.2	22
126	Advanced SiGe BiCMOS Technology for Multi-Mrad Electronic Systems. IEEE Transactions on Device and Materials Reliability, 2014, 14, 844-848.	1.5	22

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127	The Role of Atomic Displacements in Ion-Induced Dielectric Breakdown. IEEE Transactions on Nuclear Science, 2009, 56, 3210-3217.	1.2	21
128	RF Performance of Proton-Irradiated AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2014, 61, 2959-2964.	1.2	21
129	Charge Transport in Vertical GaN Schottky Barrier Diodes: A Refined Physical Model for Conductive Dislocations. IEEE Transactions on Electron Devices, 2020, 67, 841-846.	1.6	21
130	Disorder-Recrystallization Effects in Low-Energy Beam-Solid Interactions. Physical Review Letters, 2008, 100, 185502.	2.9	20
131	Effects of Metal Gates and Back-End-of-Line Materials on X-Ray Dose in ${m HfO}_{2}$ Gate Oxide. IEEE Transactions on Nuclear Science, 2011, 58, 3139-3144.	1.2	20
132	Sensitivity of High-Frequency RF Circuits to Total Ionizing Dose Degradation. IEEE Transactions on Nuclear Science, 2013, 60, 4498-4504.	1.2	20
133	Single-Event Transient Response of InGaAs MOSFETs. IEEE Transactions on Nuclear Science, 2014, 61, 3550-3556.	1.2	20
134	Electrical Stress and Total Ionizing Dose Effects on <formula formulatype="inline"><tex Notation="TeX">${hbox {MoS}}_{2}$</tex> </formula> Transistors. IEEE Transactions on Nuclear Science, 2014, 61, 2862-2867.	1.2	20
135	Quantum Mechanical Modeling of Radiation-Induced Defect Dynamics in Electronic Devices. IEEE Transactions on Nuclear Science, 2015, 62, 2169-2180.	1.2	20
136	Effects of Total-Ionizing-Dose Irradiation on SEU- and SET-Induced Soft Errors in Bulk 40-nm Sequential Circuits. IEEE Transactions on Nuclear Science, 2017, 64, 471-476.	1.2	20
137	Post-Irradiation Annealing Mechanisms of Defects Generated in Hydrogenated Bipolar Oxides. IEEE Transactions on Nuclear Science, 2008, 55, 3032-3038.	1.2	19
138	Including the Effects of Process-Related Variability on Radiation Response in Advanced Foundry Process Design Kits. IEEE Transactions on Nuclear Science, 2010, , .	1.2	19
139	Mechanisms of Interface Trap Buildup and Annealing During Elevated Temperature Irradiation. IEEE Transactions on Nuclear Science, 2011, 58, 2930-2936.	1.2	19
140	Total Ionizing Dose Effects on HfO₂-Passivated Black Phosphorus Transistors. IEEE Transactions on Nuclear Science, 2017, 64, 170-175.	1.2	19
141	Variations in Semiconductor Device Response in a Medium-Energy X-Ray Dose-Enhancing Environment. IEEE Transactions on Nuclear Science, 1987, 34, 1544-1550.	1.2	18
142	Quantum Mechanical Description of Displacement Damage Formation. IEEE Transactions on Nuclear Science, 2007, 54, 1906-1912.	1.2	18
143	Total Dose and Bias Temperature Stress Effects for HfSiON on Si MOS Capacitors. IEEE Transactions on Nuclear Science, 2007, 54, 1931-1937.	1.2	18
144	The Effects of X-Ray and Proton Irradiation on a 200 GHz/90 GHz Complementary $(npn + pnp)$ SiGe:C HBT Technology. IEEE Transactions on Nuclear Science, 2007, 54, 2190-2195.	1.2	18

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145	Effects of Hydrogen on the Radiation Response of Bipolar Transistors: Experiment and Modeling. IEEE Transactions on Nuclear Science, 2008, 55, 3039-3045.	1.2	18
146	Total Ionizing Dose Effects on FinFET-Based Capacitor-Less 1T-DRAMs. IEEE Transactions on Nuclear Science, 2010, , .	1.2	18
147	Defect Interactions of ${hbox{H}}_{2}$ in ${hbox{SiO}}_{2}$: Implications for ELDRS and Latent Interface Trap Buildup. IEEE Transactions on Nuclear Science, 2010, , .	1.2	18
148	Impact of Back-Gate Bias and Device Geometry on the Total Ionizing Dose Response of 1-Transistor Floating Body RAMs. IEEE Transactions on Nuclear Science, 2012, 59, 2966-2973.	1.2	18
149	Scaling Effects on Single-Event Transients in InGaAs FinFETs. IEEE Transactions on Nuclear Science, 2018, 65, 296-303.	1.2	18
150	Modeling Total-Dose Effects for a Low-Dropout Voltage Regulator. IEEE Transactions on Nuclear Science, 2006, 53, 3223-3231.	1.2	17
151	The Effects of Proton and X-Ray Irradiation on the DC and AC Performance of Complementary (npn +) Tj ETQq1 1 0.784314 rgBT /Overl	1.2	17
152	Multi-Scale Simulation of Radiation Effects in Electronic Devices. IEEE Transactions on Nuclear Science, 2008, 55, 1891-1902.	1.2	17
153	Trade-Offs Between RF Performance and Total-Dose Tolerance in 45-nm RF-CMOS. IEEE Transactions on Nuclear Science, 2011, 58, 2830-2837.	1.2	17
154	Understanding Charge Collection Mechanisms in InGaAs FinFETs Using High-Speed Pulsed-Laser Transient Testing With Tunable Wavelength. IEEE Transactions on Nuclear Science, 2017, 64, 2069-2078.	1.2	17
155	Gate Bias and Geometry Dependence of Total-Ionizing-Dose Effects in InGaAs Quantum-Well MOSFETs. IEEE Transactions on Nuclear Science, 2017, 64, 239-244.	1.2	17
156	Gate Bias and Length Dependences of Total Ionizing Dose Effects in InGaAs FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2019, 66, 1599-1605.	1.2	17
157	Comparison of Total-Ionizing-Dose Effects in Bulk and SOI FinFETs at 90 and 295 K. IEEE Transactions on Nuclear Science, 2019, 66, 911-917.	1.2	17
158	Total-Ionizing-Dose Response of Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 687-696.	1.2	17
159	Electrical Stress and Total Ionizing Dose Effects on Graphene-Based Non-Volatile Memory Devices. IEEE Transactions on Nuclear Science, 2012, 59, 2974-2978.	1.2	16
160	Radiation-Induced Oxide Charge in Low- and High-H$_{2}$ Environments. IEEE Transactions on Nuclear Science, 2012, 59, 755-759.	1.2	16
161	Effects of Negative-Bias-Temperature-Instability on Low-Frequency Noise in SiGe ${p}$ MOSFETs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 541-548.	1.5	16
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